AMENDMENTS TO THE CLAIMS:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A dielectric ceramic composition comprising at least

a main component containing a dielectric oxide of a composition expressed by $\{(Sr_{1-x}Ca_x)O\}_m \cdot (Ti_{1-y}Zr_y)O_2$ and

a first subcomponent containing at least one type of compound selected from oxides of V, Nb, W, Ta, and Mo and/or compounds forming these oxides after firing, wherein

the symbols m, x, and y showing the molar ratio of the composition in the formula contained in the main component are in relations of

$0.94<m<1.08$,

$0\le x\le 1.00$, and

$0\le y\le 0.20$ and

the ratio of the first subcomponent with respect to 100 moles of the main component, which is converted to the metal element in the oxide, is 0.01 mole≤first subcomponent<2 ~~moles.~~moles, and

wherein the dielectric ceramic composition is obtained by performing heat treatment in an atmosphere having an oxygen partial pressure of 10^{-1} Pa to 10 Pa after firing in a reducing atmosphere.

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2. (Original) The dielectric ceramic composition as set forth in claim 1, further comprising a second subcomponent containing an oxide of Mn and/or a compound forming an oxide of Mn after firing, wherein

the ratio of the second subcomponent with respect to 100 moles of the main component, which is converted to the metal element in the oxide, is 0 mole≤second subcomponent<4 moles.

3. (Original) The dielectric ceramic composition as set forth in claim 1,

further comprising a third subcomponent containing at least one type of compound selected from SiO_2, MO, Li_2O, and B_2O_3, where M is at least one element selected from Ba, Ca, Sr, and Mg, wherein

the ratio of the third subcomponent with respect to 100 moles of the main component, which is converted to oxide, is 0 mole<third subcomponent<15 moles.

4. (Original) The dielectric ceramic composition as set forth in claim 2,

further comprising a third subcomponent containing at least one type of compound selected from SiO_2, MO, Li_2O, and B_2O_3, where M is at least one element selected from Ba, Ca, Sr, and Mg, wherein

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the ratio of the third subcomponent with respect to 100 moles of the main component, which is converted to oxide, is 0 mole<third subcomponent<15 moles.

5. (Original) The dielectric ceramic composition as set forth in claim 1, wherein the rate of change of the electrostatic capacity with respect to temperature ΔC is 2000 ppm/°C to 0 ppm/°C at least in the temperature range of 20°C to 85°C, where the reference temperature of the electrostatic capacity C is 20°C.

6. (Original) The dielectric ceramic composition as set forth in claim 2, wherein the rate of change of the electrostatic capacity with respect to temperature ΔC is 2000 ppm/°C to 0 ppm/°C at least in the temperature range of 20°C to 85°C, where the reference temperature of the electrostatic capacity C is 20°C.

7. (Original) The dielectric ceramic composition as set forth in claim 3, wherein the rate of change of the electrostatic capacity with respect to temperature ΔC is 2000 ppm/°C to 0 ppm/°C at least in the temperature range of 20°C to 85°C, where the reference temperature of the electrostatic capacity C is 20°C.

8. (Original) The dielectric ceramic composition as set forth in claim 4, wherein the rate of change of the electrostatic capacity with respect to temperature ΔC is 2000 ppm/°C to 0 ppm/°C at least in the temperature range of 20°C to 85°C, where the reference temperature of the electrostatic capacity C is 20°C.

9. (Currently Amended) An electronic device having a dielectric layer, wherein

said dielectric layer is comprised of a dielectric ceramic composition and

said dielectric ceramic composition comprises at least

a main component containing a dielectric oxide of a composition expressed by $\{(Sr_{1-x}Ca_x)O\}m\cdot(Ti_{1-y}Zr_y)O_2$ and

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a first subcomponent containing at least one type of compound selected from oxides of V, Nb, W, Ta, and Mo and/or compounds forming these oxides after firing, wherein

the symbols m, x, and y showing the molar ratio of the composition in the formula contained in the main component are in relations of

$0.94<m<1.08$,

$0\leq x\leq 1.00$, and

$0\leq y\leq 0.20$ and

the ratio of the first subcomponent with respect to 100 moles of the main component, which is converted to the metal element in the oxide, is 0.01 mole≤ first subcomponent<2 ~~moles.~~moles, and

wherein the dielectric ceramic composition is obtained by performing heat treatment in an atmosphere having an oxygen partial pressure of 10^{-1} Pa to 10 Pa after firing in a reducing atmosphere.

10. (Original) The electronic device as set forth in claim 9, provided with a capacitor device body comprised of said dielectric layers and internal electrode layers alternately stacked.

11. (New) The electronic device as set forth in claim 9,

further comprising a second subcomponent containing an oxide of Mn and/or a compound forming an oxide of Mn after firing, wherein

the ratio of the second subcomponent with respect to 100 moles of the main component, which is converted to the metal element in the oxide, is a 0 mole≤second subcomponent<4 moles.

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12. (New) The electronic device as set forth in claim 9,

further comprising a third subcomponent containing at least one type of compound selected from SiO_2, MO (where M is at least one element selected from Ba, Ca, Sr, and Mg), Li_2O, and B_2O_3, wherein

the ratio of the third subcomponent with respect to 100 moles of the main component, which is converted to oxide, is 0 mole<third subcomponent < 15 moles.

13. (New) The electronic device as set forth in claim 9,

wherein the rate of change of the electrostatic capacity with respect to temperature (ΔC) is –2000 ppm/°C to 0 ppm/°C at least in the temperature range of 20°C to 85°C, with the reference temperature of the electrostatic capacity C being 20°C.